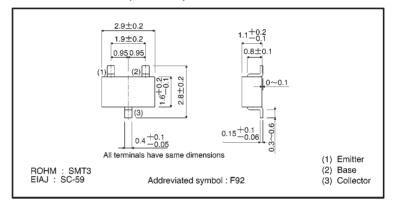
Digital transistors (built in resistor) DTB123TK

Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thinfilm resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.
- Higher mounting densities can be achieved.

External dimensions (Units: mm)



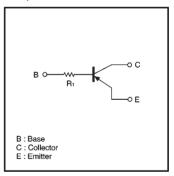
Structure

PNP digital transistor (Built-in resistor type)

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CBO} —50		V
Collector-emitter voltage	V _{CEO} -40		V
Emitter-base voltage	V _{EBO}	- 5	V
Collector current	lc	Ic —500	
Collector power dissipation	Pc	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55∼+150	°C

■Equivalent circuit



Transistors DTB123TK

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-50	_	_	٧	Ic=-50 μ A
Collector-emitter breakdown voltage	BVCEO	-40	_	_	V	Ic=-1mA
Emitter-base breakdown voltage	ВУево	-5	_	_	V	IE=-50 μ A
Collector cutoff current	Ісво	_	_	-0.5	μΑ	V _{CB} =-50V
Emitter cutoff current	ІЕВО	_	_	-0.5	μΑ	V _{EB} =-4V
Collector-emitter saturation voltage	VCE(sat)	_	_	-0.3	٧	Ic/I _B =-50mA/-2.5mA
DC current transfer ratio	hfe	100	250	600	_	V _{CE} =-5V, I _C =-50mA
Input resistance	R ₁	1.54	2.2	2.86	kΩ	
Transition frequency	fτ	_	200	_	MHz	V _{CE} =-10V, I _E =50mA, f=100MHz *

^{*} Transition frequency of the device

Packaging specifications

	Package	SMT3
	Packaging type	Taping
	Code	T146
Part No.	Basic ordering unit (pieces)	3000
DTB123TK		0

Electrical characteristic curves

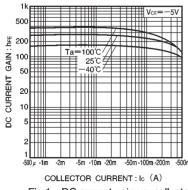


Fig.1 DC current gain vs. collector current

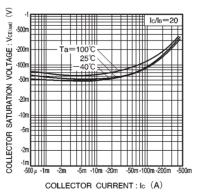


Fig.2 Collector-emitter saturation voltage vs. collector current